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2        ABSTRACT OF THE DISCLOSURE  
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4    A method for maximizing the interfacial properties of  
5    magnetoresistive sensors, such as spin valve and GMR sensors used  
6    in storage devices, comprises selecting the materials for  
7    ferromagnetic layers and for electrically conductive spacers that  
8    are interposed between the ferromagnetic layers.    The  
9    electronegativities of the selected materials are substantially  
10   matched so that an absolute value of the differences in  
11   electronegativities is minimized.    The conductive spacer material  
12   provides a relatively low resistivity and a large mean free path.  
13   The sensors experience greater chemical and thermal stability,  
14   are corrosion resistant, and realize an increased signal output.